



N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
150	0.052 at V _{GS} = 10 V	28		
	0.060 at V _{GS} = 6 V	26		

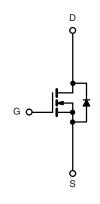
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC

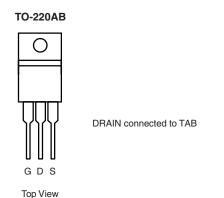


APPLICATIONS

· Primary Side Switch



N-Channel MOSFET



Ordering Information: SUP28N15-52 E3 (Lead (Pb)-free)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	150	V
Gate-Source Voltage		V _{GS}	± 20	_ v
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I-	28	
	T _C = 125 °C	I _D	16	
Pulsed Drain Current		I _{DM}	50	Α
Continuous Source Current (Diode Conduction)		I _S	28	
Avalanche Current		I _{AR}	25	
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	31	mJ
Maximum Power Dissipation	T _C = 25 °C		120 ^b	
	$T_A = 25 ^{\circ}C$ (mounted) ^a	P _D	3.75 ^a	W
Operating Junction and Storage Temperature Range	T _J , T _{stq}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Unit		
Junction-to-Ambient ^a	PCB Mount ^a	R _{thJA}	40	°C/W		
Junction-to-Ambient*	Free Air		62.5			
Junction-to-Case (Drain)		R _{thJC}	1.25]		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.

SUP28N15-52

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					<u>l</u>		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	150			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 120 V, V _{GS} = 0 V			1	μΑ	
	I_{DSS}	V _{DS} = 120 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 5 A		0.042	0.052		
h	В	V _{GS} = 10 V, I _D = 5 A, T _J = 125 °C			0.109		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A, T _J = 175 °C			0.145	Ω	
		V _{GS} = 6 V, I _D = 5 A		0.047	0.060		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 25 A		40		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1725		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		216			
Reverse Transfer Capacitance	C _{rss}			100			
Total Gate Charge ^c	Q_g			33	40	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 28 \text{ A}$		9			
Gate-Drain Charge ^c	Q_{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			15	25	ns	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 3 Ω I_D \cong 28 A, V_{GEN} = 10 V, R_g = 2.5 Ω		70	100		
Turn-Off Delay Time ^c	t _{d(off)}			25	40		
Fall Time ^c	t _f			60	90		
Source-Drain Diode Ratings and Cha	racteristics 7	T _C = 25 °C					
Pulsed Current	I _{SM}				50	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 25 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 28 A, dl/dt = 100 A/μs		95	140	ns	

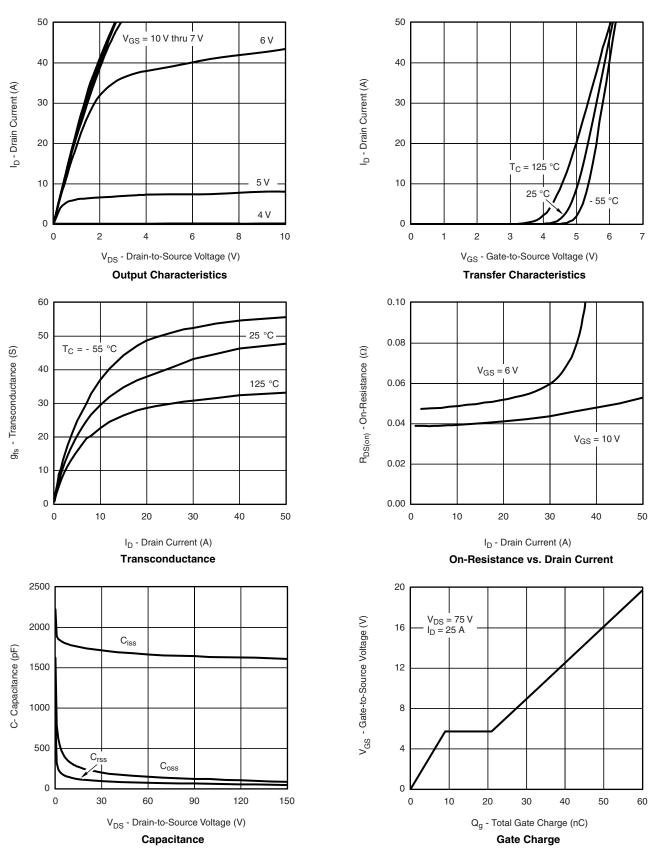
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



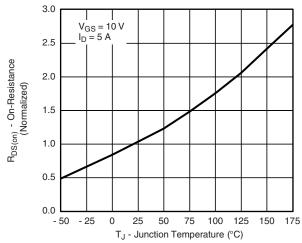
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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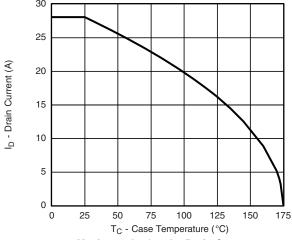


On-Resistance vs. Junction Temperature

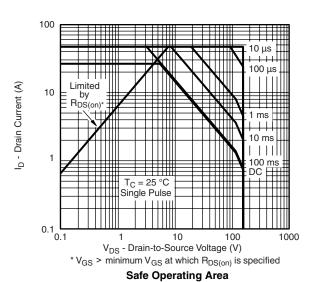
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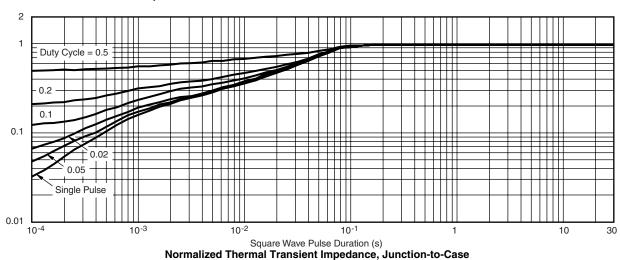
Source-Drain Diode Forward Voltage

THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature





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Normalized Effective Transient Thermal Impedance



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